

2-Input NAND Gate with Open Drain Output

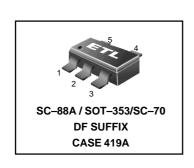
MC74VHC1G01

The MC74VHC1G01 is an advanced high speed CMOS 2-input NAND gate with an open drain output fabricated with silicon gate CMOS technology. It achieves high speed peration similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including an open drain output which provides the ability to set output switching level. This allows the MC74VHC1G01 to be used to interface 5 V circuits to circuits of any voltage between V cc and 7 V using an external resistor and power supply.

The MC74VHC1G01 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage.

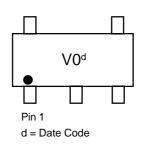
- High Speed: $t_{PD} = 3.7 \text{ ns (Typ)}$ at $V_{CC} = 5 \text{ V}$
- Low Internal Power Dissipation: I cc = 2 mA (Max) at T A = 25°C
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16

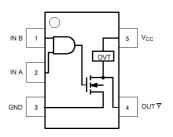




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MARKING DIAGRAMS





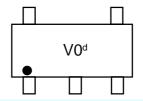




Figure 1. Pinout (Top View)

Pin 1 d = Date Code

Figure 2. Logic Symbol

V_{cc}

FUNCTION TABLE

Inp	outs	Output
Α	В	Y
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.



MC74VHC1G00

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{cc}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{IN}	DC Input Voltage		- 0.5 to 7.0	V
V _{OUT}	DC Output Voltage		- 0.5 to 7.0	V
I _{IK}	DC Input Diode Current		-20	mA
I ok	DC Output Diode Current	V_{out} < GND; V_{out} > V_{cc}	+20	mA
I _{OUT}	DC Output Sink Current		+ 25	mA
I _{cc}	DC Supply Current per Supply Pin		+50	mA
P _D	Power dissipation in still air	SC-88A, TSOP-5	200	mW
θ JA	Thermal resistance	SC-88A, TSOP-5	333	°C/W
Τ _L	Lead Temperature, 1 mm from Case for	10 Seconds	260	°C
ΤJ	Junction Temperature Under Bias		+ 150	°C
T _{stg}	Storage temperature		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2)	>2000	V
		Machine Model (Note 3)	> 200	
		Charged Device Model (Note 4)	N/A	
I LATCH-UP	Latch-Up Performance Above V cc and	d Below GND at 125°C (Note 5)	± 500	mA

- 1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.
- 2. Tested to EIA/JESD22-A114-A
- 3. Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit		
V _{cc}	DC Supply Voltage		2.0	5.5	V	
V IN	DC Input Voltage	0.0	5.5	V		
V _{OUT}	DC Output Voltage		0.0	7.0	V	
T _A	Operating Temperature Range		– 55	+ 125	°C	
tr,tf	Input Rise and Fall Time	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	0	100	ns/V	
		$V_{CC} = 5.0 \pm 0.5 V$	0	20		

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction	Junction Time,	
Temperature °C	Hours	Years
80	1,032,200	117.8
90	419,300	47.9
100	100 178,700	
110	79,600	9.4
120	120 37,000	
130	130 17,800	
140	8,900	1.0

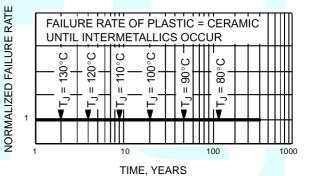


Figure 3. Failure Rate vs. Time Junction Temperature



MC74VHC1G01

DC ELECTRICAL CHARACTERISTICS

			V cc	Т	_A = 25	°C	T _A ≤	85 °C	–55 °C t	o 125 °C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level		2.0	1.5			1.5		1.5		٧
	Input Voltage		3.0	2.1			2.1		2.1		
			4.5	3.15			3.15		3.15		
			5.5	3.85			3.85		3.85		
V _{IL}	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0			0.9		0.9		0.9	
			4.5			1.35		1.35		1.35	
			5.5			1.65		1.65		1.65	
V _{OH}	Minimum High-Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0	1.9	2.0		1.9		1.9		V
	Output Voltage	$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9		2.9		
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		4.5	4.4	4.0		4.4		4.4		
		$V_{IN} = V_{IH} \text{ or } V_{IL}$									Ī
		$I_{OH} = -4 \text{ mA}$	3.0	2.58			2.48		2.34		
		$I_{OH} = -8 \text{ mA}$	4.5	3.94			3.80		3.66		
V _{OL}	Maximum Low-Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0		0.0	0.1		0.1		0.1	V
	Output Voltage	$I_{OL} = 50 \mu A$	3.0		0.0	0.1		0.1		0.1	
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		4.5		0.0	0.1		0.1		0.1	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$									Ī
		$I_{OL} = 4 \text{ mA}$	3.0			0.36		0.44		0.52	
		$I_{OL} = 8 \text{ mA}$	4.5			0.36		0.44		0.52	
I _{IN}	Maximum Input	$V_{IN} = 5.5 V \text{ or GND}$	0 to5.5			±0.1		±1.0		±1.0	μΑ
	Leakage Current										
I _{cc}	Maximum Quiescent	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μΑ
	Supply Current										
I OPD	Maximum Off-state	V OUT = 5.5 V	0			0.25		2.5		5.0	μΑ
	Leakage Current										

AC ELECTRICAL CHARACTERISTICS C $_{load}$ = 50 pF, Input t $_{r}$ = t $_{f}$ = 3.0 ns

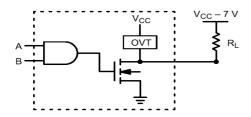
			T _A = 25 °C			$T_A = 25^{\circ}C$ $T_A \le 85^{\circ}C$ $55^{\circ}C$ to 1		125 °C		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t PZL	Maximum Output	V CC = 3.3 ± 0.3 V C L = 15 pF		5.5	7.9		9.5		11.0	ns
	Enable Time,	$R \perp = R \mid = 500 \Omega$ $C \perp = 50 pF$		8.0	11.4		13.0		15.5	
	Input A or B to Y									
		V CC = 5.0 ± 0.5 V C L = 15 pF		3.7	5.5		6.5		8.0	
		$R L = R I = 500 \Omega$ $C L = 50 pF$		5.2	7.5		8.5		8.0	
t PLZ	Maximum Output	V CC = 3.3 ± 0.3 V C L = 50 pF		8.0	11.4		13.0		15.5	ns
	Disable Time	R L = R I = 500 Ω								
		V CC = 5.0 ± 0.5 V C L = 50 pF		5.2	7.5		8.5		10.0	
		R L = R I = 500 Ω			1					
C IN	Maximum Input			4	10		10		10	pF
	Capacitance									

		Typical @ 25°C, V _{cc} = 5.0 V	
С	Power Dissipation Capacitance (Note 6)	18	pF

^{6.} C $_{PD}$ is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I $_{CC(OPR)} = C _{PD} X V _{CC} X f _{in} + I _{CC} . C _{PD}$ is used to determine the no-load dynamic power consumption; P $_{D} = C _{PD} X V _{CC} ^2 X f _{in} + I _{CC} X V _{CC}$.



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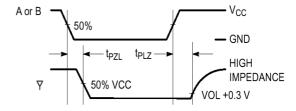
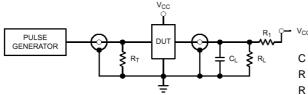


Figure 4. Output Voltage Mismatch Application

Figure 5. Switching Waveforms

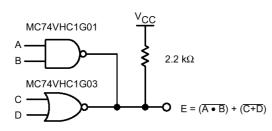


C L = 50 pF equivalent (Includes jig and probe capacitance)

R L = R 1 = 500Ω or equivalent

R T = Z OUT of pulse generator (typically 50 Ω)

Figure 6. Test Circuit



B 1 5 R LED

Figure 7. Complex Boolean Functions

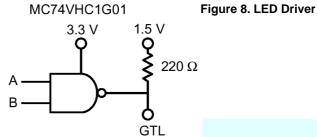


Figure 9. GTL Driver

DEVICE ORDERING INFORMATION

Device Order Number	Logic Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size
MC74VHC1G01DFT1	МС	74	VHC1G	01	DF	T1	SC-70/SC-88A/ SOT-353	178 mm (7 in) 3000 Unit
MC74VHC1G01DFT2	MC	74	VHC1G	01	DF	T2	SC-70/SC-88A/ SOT-353	178 mm (7 in) 3000 Unit
MC74VHC1G01DFT4	MC	74	VHC1G	01	DF	T4	SC-70/SC-88A/ SOT-353	330 mm (13 in) 10,000 Unit
MC74VHC1G01DTT1	MC	74	VHC1G	01	DT	T1	SOT-23/TSOPS/ SC-59	178 mm (7 in) 3000 Unit
MC74VHC1G01DTT3	MC	74	VHC1G	01	DT	ТЗ	SOT-23/TSOPS/ SC-59	330 mm (13 in) 10,000 Unit